HMC565LC5

v04.0118

GaAs SMT PHEMT LOW NOISE AMPLIFIER, 6 - 20 GHz

Typical Applications

The HMC565LC5 is ideal for use as a LNA or driver amplifier for:

- Point-to-Point Radios
- Point-to-Multi-Point Radios & VSAT
- Test Equipment and Sensors
- Military & Space

Features

Noise Figure: 2.5 dB

Gain: 21 dB

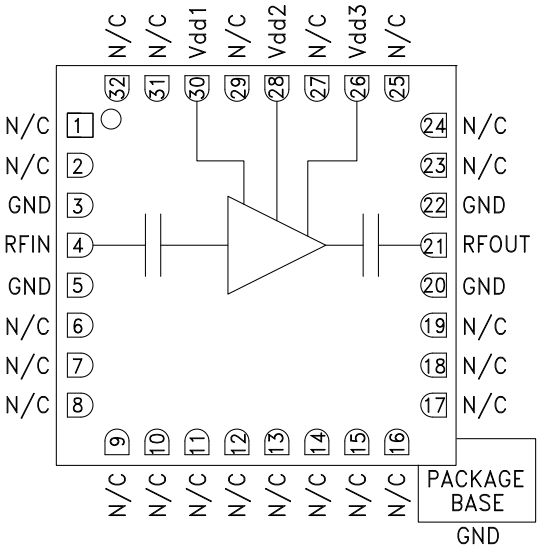
OIP3: 20 dBm

Single Supply: +3V @ 53 mA

50 Ohm Matched Input/Output

RoHS Compliant 5 x 5 mm Package

Functional Diagram



General Description

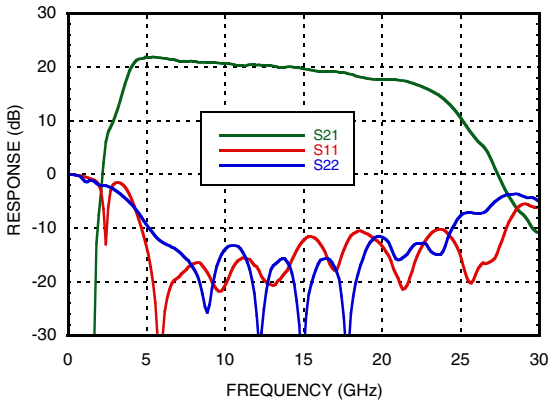
The HMC565LC5 is a high dynamic range GaAs pHEMT MMIC Low Noise Amplifier housed in a leadless RoHS compliant 5x5mm SMT package. Operating from 6 to 20 GHz, the HMC565LC5 features 21 dB of small signal gain, 2.5 dB noise figure and IP3 of +20 dBm across the operating band. This self-biased LNA is ideal for microwave radios due to its single +3V supply operation, and DC blocked RF I/O's.

Electrical Specifications, T_A = +25° C, Vdd 1, 2, 3 = +3V

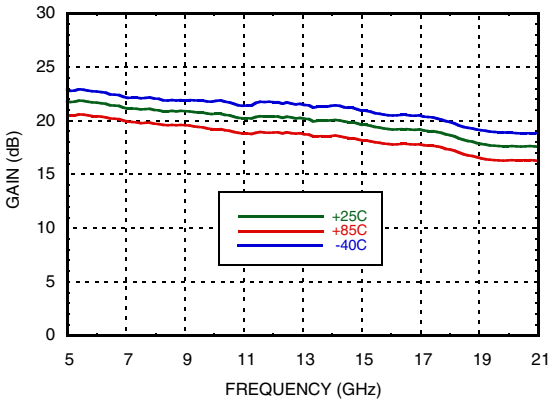
Parameter	Min.	Typ.	Max.	Min.	Typ.	Max.	Units
Frequency Range		6 - 12			12 - 20		GHz
Gain	19	21		16	18.5		dB
Gain Variation Over Temperature		0.025	0.035		0.025	0.035	dB/ °C
Noise Figure		2.5	2.8		2.5	3	dB
Input Return Loss		15			12		dB
Output Return Loss		13			15		dB
Output Power for 1 dB Compression (P1dB)	8	10		9	11		dBm
Saturated Output Power (Psat)		11			13		dBm
Output Third Order Intercept (IP3)		20			21		dBm
Total Supply Current (Idd)(Vdd = +3V)		53	75		53	75	mA

For price, delivery, and to place orders: Analog Devices, Inc., One Technology Way, P.O. Box 9106, Norwood, MA 02062-9106
Phone: 781-329-4700 • Order online at www.analog.com
Application Support: Phone: 1-800-ANALOG-D

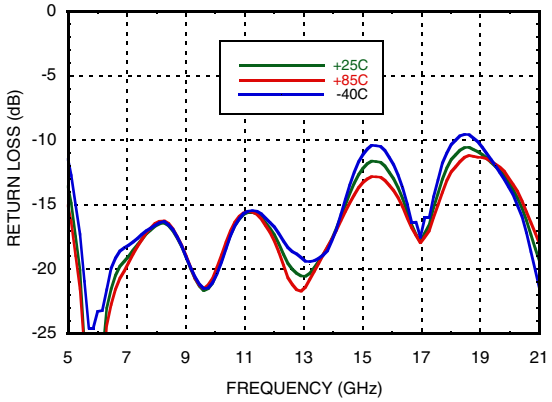
Broadband Gain & Return Loss



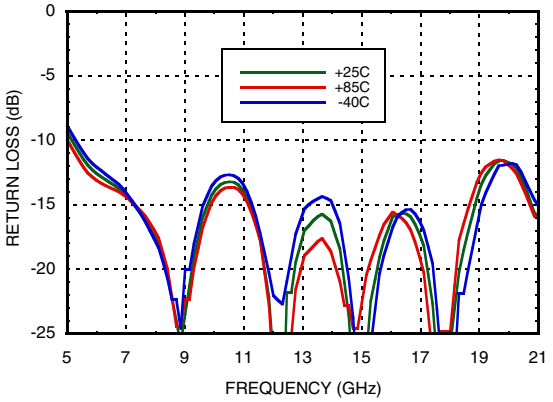
Gain vs. Temperature



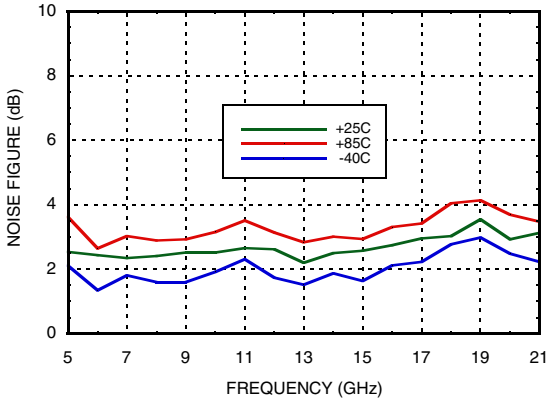
Input Return Loss vs. Temperature



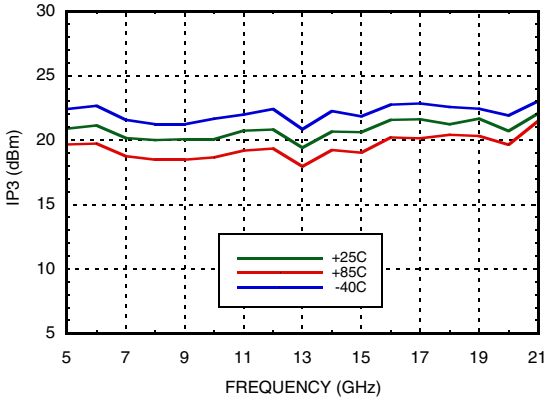
Output Return Loss vs. Temperature



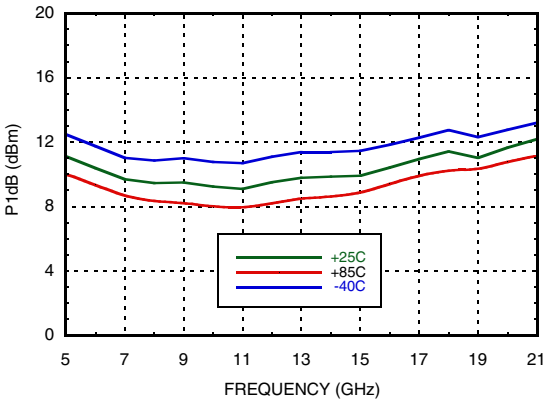
Noise Figure vs. Temperature



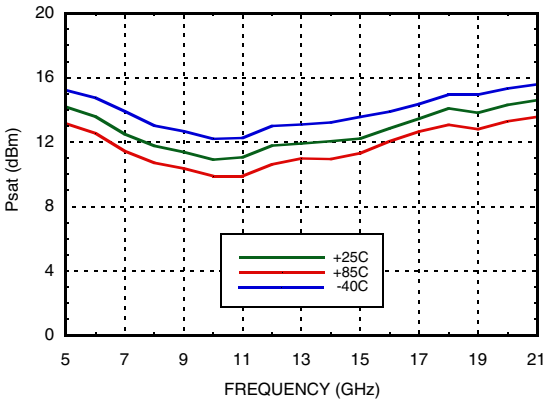
Output IP3 vs. Temperature



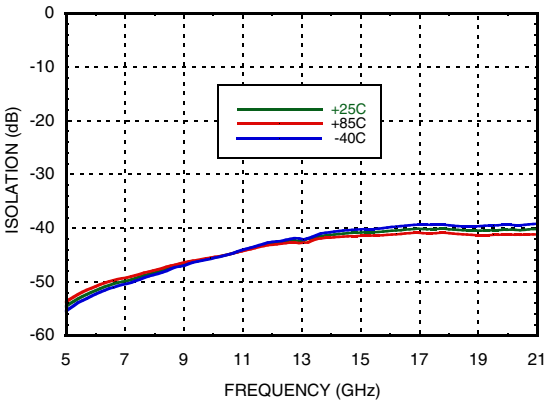
P1dB vs. Temperature



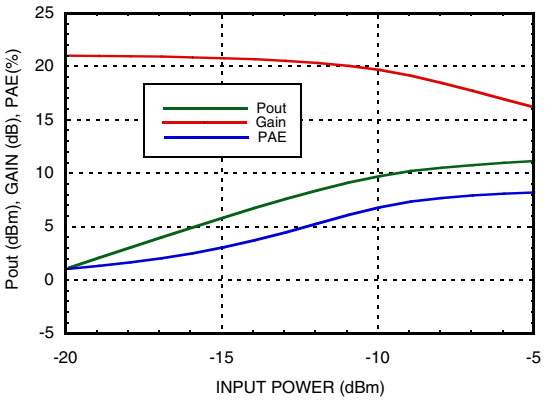
Psat vs. Temperature



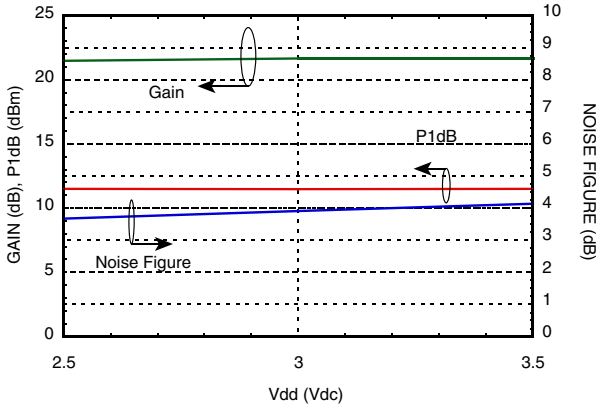
Reverse Isolation vs. Temperature



Power Compression @ 12 GHz



Gain, Noise Figure & Power vs. Supply Voltage @ 12 GHz



Absolute Maximum Ratings

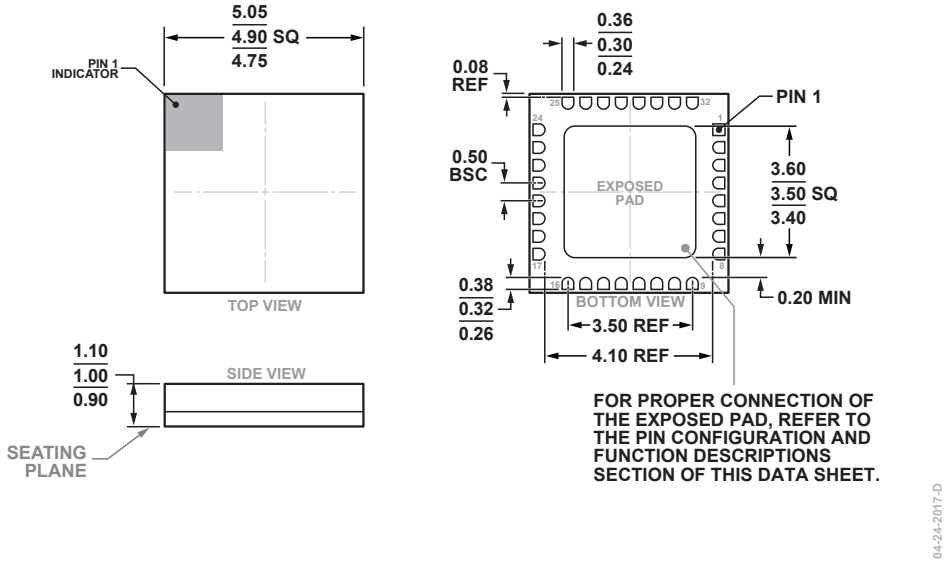
Drain Bias Voltage (Vdd1, Vdd2, Vdd3)	+3.5 Vdc
RF Input Power (RFIN)(Vdd = +3.0 Vdc)	10 dBm
Channel Temperature	175 °C
Continuous Pdiss (T= 85 °C) (derate 8.5 mW/°C above 85 °C)	0.753 W
Thermal Resistance (channel to ground paddle)	119.5 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +85 °C
ESD Sensitivity (HBM)	Class 1A

Typical Supply Current vs. Vdd

Vdd (V)	Idd (mA)
+2.5	51
+3.0	53
+3.5	56

ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS

Outline Drawing



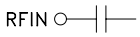
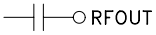
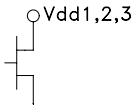
32-Terminal Ceramic Leadless Chip Carrier [LCC]
(E-32-1)
Dimensions shown in millimeters.

ORDERING GUIDE

Part Number	Package Material	Lead Finish	MSL Rating [1]	Package Marking [2]
HMC565LC5	Alumina, White	Gold over Nickle	MSL3	H565 XXXX
HMC565LC5TR	Alumina, White	Gold over Nickle	MSL3	H565 XXXX
HMC565LC5TR-R5	Alumina, White	Gold over Nickle	MSL3	H565 XXXX

[1] Max peak reflow temperature of 260 °C
[2] 4-Digit lot number XXXX

Pin Descriptions

Pin Number	Function	Description	Interface Schematic
1, 2, 6 - 19, 23 - 25, 27, 29, 31, 32	N/C	This pin may be connected to RF/DC ground. Performance will not be affected.	
3, 5, 20, 22	GND	These pins and package bottom must be connected to RF/DC ground.	
4	RFIN	This pin is AC coupled and matched to 50 Ohms.	
21	RFOUT	This pin is AC coupled and matched to 50 Ohms.	
30, 28, 26	Vdd1, 2, 3	Power Supply Voltage for the amplifier. External bypass capacitors of 100 pF and 2.2 µF are required.	

Application Circuit

Component	Value
C1, C2, C3	100 pF
C4, C5, C6	2.2 µF